NPN Epitaxial Silicon Transistor

KSC1008

Features

- Low-Frequency Amplifier Medium Speed Switching
- High Collector–Base Voltage: V_{CBO} = 80 V
- Collector Current: $I_C = 700 \text{ mA}$
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)
- Non Suffix "-C" means Side Collector (1. Emitter 2. Base 3. Collector)
- Complement to KSA708
- These are Pb–Free Devices

ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	80	V	
V _{CEO}	Collector-Emitter Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	8	V	
Ι _C	Collector Current	700	mA	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	–55 to 150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted.})$ (Note 1)

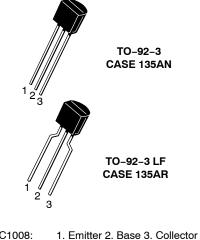
Symbol	Parameter	Value	Unit
PD	Power Dissipation	800	mW
	Derate Above 25°C	6.4	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	156	°C/W

1. PCB size: FR-4, 76 mm \times 114 mm \times 1.57 mm (3.0 inch \times 4.5 inch \times 0.062 inch) with minimum land pattern size.



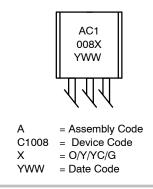
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KSC1008:1. Emitter 2. Base 3. CollectorKSC1008C:1. Emitter 2. Collector 3. Base

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

KSC1008

ELECTRICAL CHARACTERISTICS (T_A = $25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$	80	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA, I _B = 0	60	-	-	V
BV_{EBO}	Emitter-Base Breakdown Voltage	I _E = 10 μA, I _C = 0	8	-	-	V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = 60 \text{ V}, \text{ I}_{E} = 0$	-	-	0.1	μA
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = 5 V, I_{C} = 0$	-	-	0.1	μA
h _{FE}	DC Current Gain	$V_{CE} = 2 V, I_{C} = 50 mA$	40	-	400	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500 mA, I _B = 50 mA	-	0.2	0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 500 mA, I _B = 50 mA	-	0.86	1.10	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 50 \text{ mA}$	30	50	-	MHz
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz	-	8	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

h_{FE} Classification

Classification	0	Y	G
hFE	70 ~ 140	120 ~ 240	200 ~ 400

ORDERING INFORMATION (Note 2)

Part Number	Top Mark	Package	Shipping
KSC1008OBU	C1008 O-	TO-92-3	10000 / Bulk Bag
KSC1008YBU	C1008 Y-	(Pb-Free)	10000 / Bulk Bag
KSC1008YTA	C1008 Y-	TO-92-3 LR	2000 / Fan-Fold
KSC1008CYTA	C1008 YC	(Pb-Free)	2000 / Fan-Fold
KSC1008GTA	C1008 G-		2000 / Fan-Fold

 Affix "-C-" means center collector pin. Affix "-O-, -Y-, -G-" means h_{FE} classification. Suffix "-BU" means bulk packing, straight lead form. Suffix "-TA" means tape and ammo packing, 0.200 in-line spacing lead form.

KSC1008

TYPICAL PERFORMANCE CHARACTERISTICS

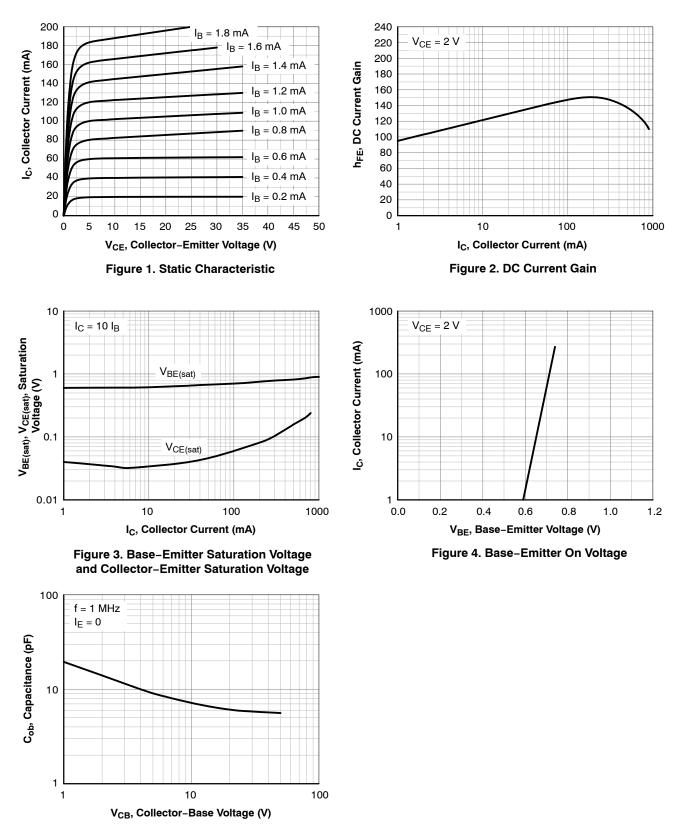
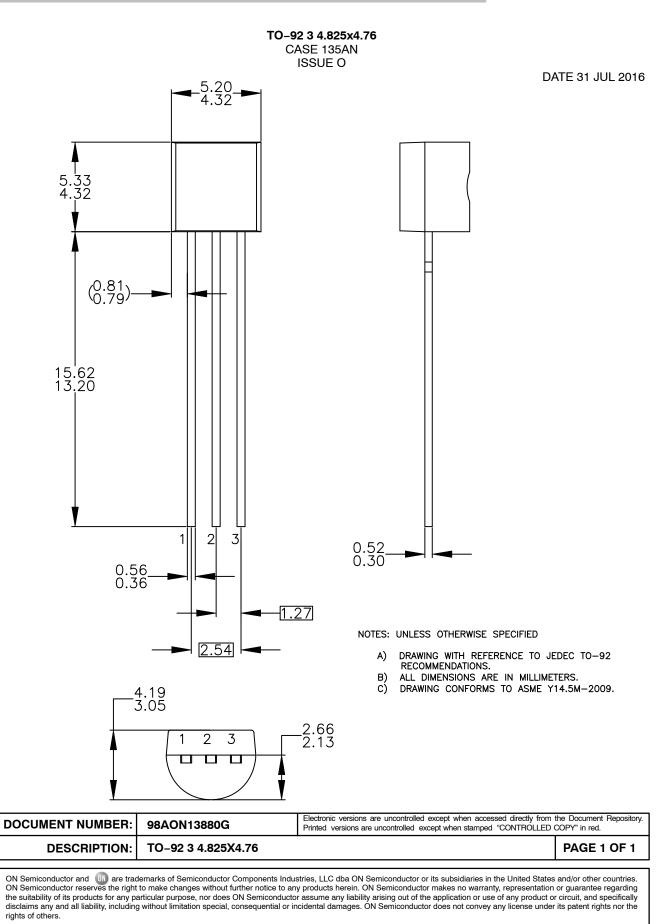


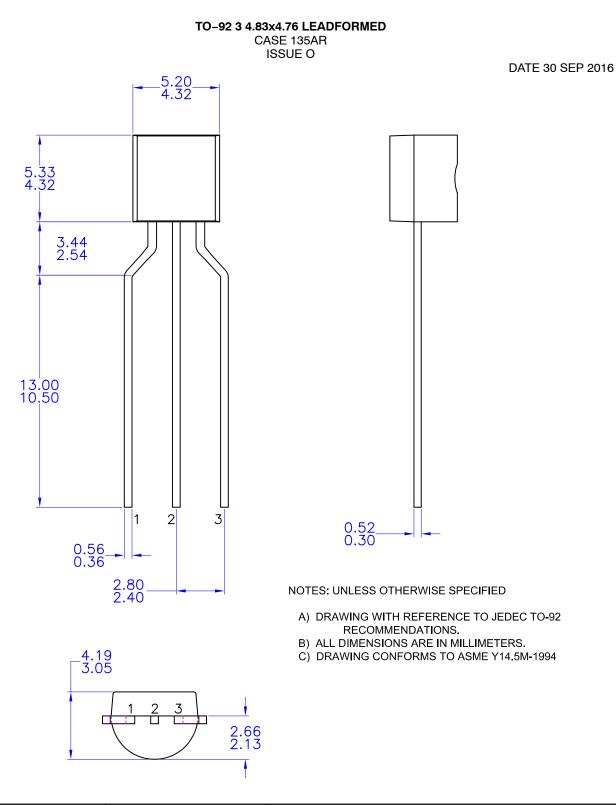
Figure 5. Collector Output Capacitance





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